2SA683 / 2SA684 PNP Silicon Epitaxial Planar Transistor

for low frequency power amplification and driver amplification

The transistor is subdivided into three group, Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



 Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

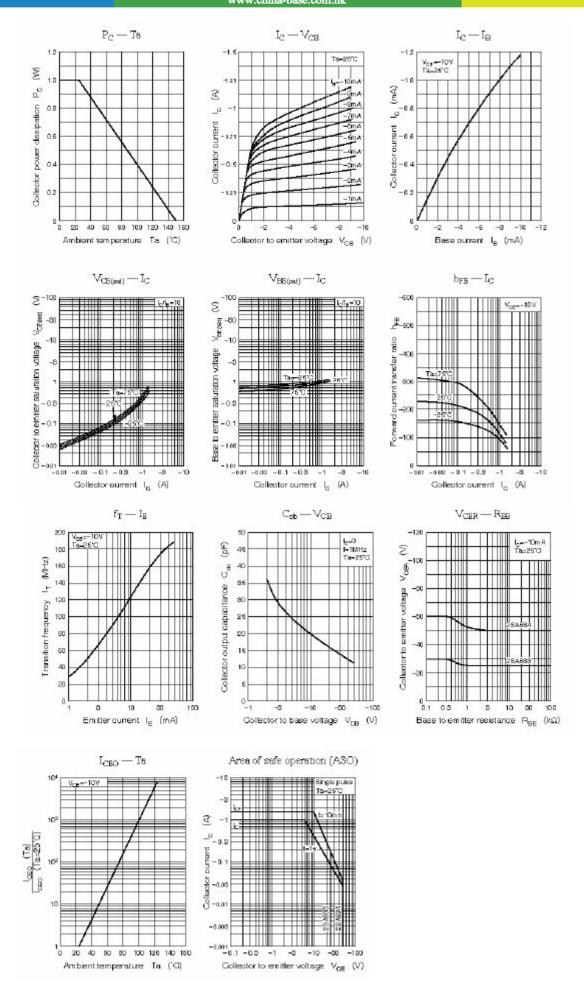
Absolute Maximum Ratings (Ta = 25 °C)

Parameter		Symbol	Value	Unit	
Collector Base Voltage	2SA683 2SA684	-V _{CBO}	30 50	V	
Collector Emitter Voltage	2SA683 2SA684	-V _{CEO}	25 40	V	
Emitter Base Voltage		-V _{EBO}	5	V	
Collector Current		-I _C	1	А	
Peak Collector Current		-I _P	1.5	А	
Power Dissipation		P _{tot}	1	W	
Junction Temperature		T _j	150	°C	
Storage Temperature Range		Ts	- 55 to + 150	°C	

Characteristics at T_{amb} = 25 °C

Parameter		Min.	Тур.	Max.	Unit
DC Current Gain					
at -V _{CE} = 10 V, -I _C = 500 mA Current Gain Group C	h _{FE}	85	-	170	-
F	R h _{FE}	120	-	240	-
	h _{FE}	170	-	340	-
at $-V_{CE} = 5 \text{ V}$, $-I_{C} = 1 \text{ A}$	h _{FE}	50	-	-	-
Collector Cutoff Current at -V _{CB} = 20 V	-I _{CBO}	-	-	0.1	μΑ
Collector Base Breakdown Voltage 2SA683	\/	30	-	-	V
at $-I_C = 10 \mu\text{A}$ 2SA684	-V (BR)CBO	50	-	-	V
Collector Emitter Breakdown Voltage 2SA683	V	25	-	-	V
at $-I_C = 2 \text{ mA}$ 2SA684	-V (BR)CEO	40	-	-	V
Emitter Base Breakdown Voltage at $-I_C = 10 \mu A$	-V _{(BR)EBO}	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 500 \text{ mA}$, $-I_B = 50 \text{ mA}$	-V _{CEsat}	-	-	0.4	>
Base Emitter Saturation Voltage at $-I_C = 500 \text{ mA}$, $-I_B = 50 \text{ mA}$	-V _{BEsat}	-	-	1.2	>
Transition Frequency at $-V_{CB} = 10 \text{ V}$, $I_E = 50 \text{ mA}$, $f = 200 \text{ MHz}$	f _T	-	200	-	MHz
Collector Output Capacitance at $-V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$	C _{ob}	-	-	30	pF

Page 1 of 2



Page 2 of 2